

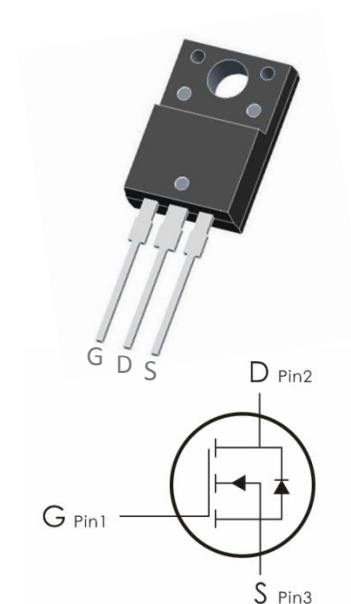
Description:

This N-Channel MOSFET uses advanced Planar technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=650V, I_D=8A, R_{DS(ON)} < 1300m\Omega @ V_{GS}=10V$ (Typ: $1100m\Omega$)
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
DOPF8N65	8N65	TO- 220F	50 pcs/Tube

Absolute Maximum Ratings: ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Continuous Drain Current	8	A
	Continuous Drain Current- $T_C=100^\circ\text{C}$	4.4	
I_{DM}	Pulsed Drain Current ¹	28	
P_D	Power Dissipation	48	W
E_{AS}	Single pulse avalanche energy ²	247	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	$^\circ\text{C}$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	2.6	$^\circ\text{C}/\text{W}$

Electrical Characteristics: ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250 μ A	650	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =650V	---	---	1	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 30V, V _{DS} =0A	---	---	± 100	nA
On Characteristics						
V _{GS(th)}	Gate-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μ A	2	---	4	V
R _{DS(ON)}	Drain-Source On Resistance ³	V _{GS} =10V, I _D =3A	---	1100	1300	m Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1MHz	---	997.5	---	pF
C _{oss}	Output Capacitance		---	94.5	--	
C _{rss}	Reverse Transfer Capacitance		---	4.7	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DS} =325V, I _D =7A, R _{ENG} =9.1 Ω ,V _{GS} =10V	---	11	---	ns
t _r	Rise Time		---	10	---	ns
t _{d(off)}	Turn-Off Delay Time		---	36	---	ns
t _f	Fall Time		---	18	---	ns
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =320V, I _D =7A	---	24	---	nC
Q _{gs}	Gate-Source Charge		---	5	---	nC
Q _{gd}	Gate-Drain “Miller” Charge		---	8	---	nC
Drain-Source Diode Characteristics						
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _{SD} =7A	---	---	1.5	V
I _S	Continuous Drain Curren	V _D =V _G =0V	---	---	8	A
I _{SM}	Pulsed Drain Current		---	---	28	A
T _{rr}	Reverse Recovery Time	I _F =7A, T _J =25℃	---	280	---	ns
Q _{rr}	Reverse Recovery Charge	di/dt=100A/us	---	1.2	---	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition : $T_J=25^{\circ}\text{C}$, $V_{DD}=325\text{V}$, $V_G=10\text{V}$, $L=0.5\text{mH}$
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$

Typical Characteristics: ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

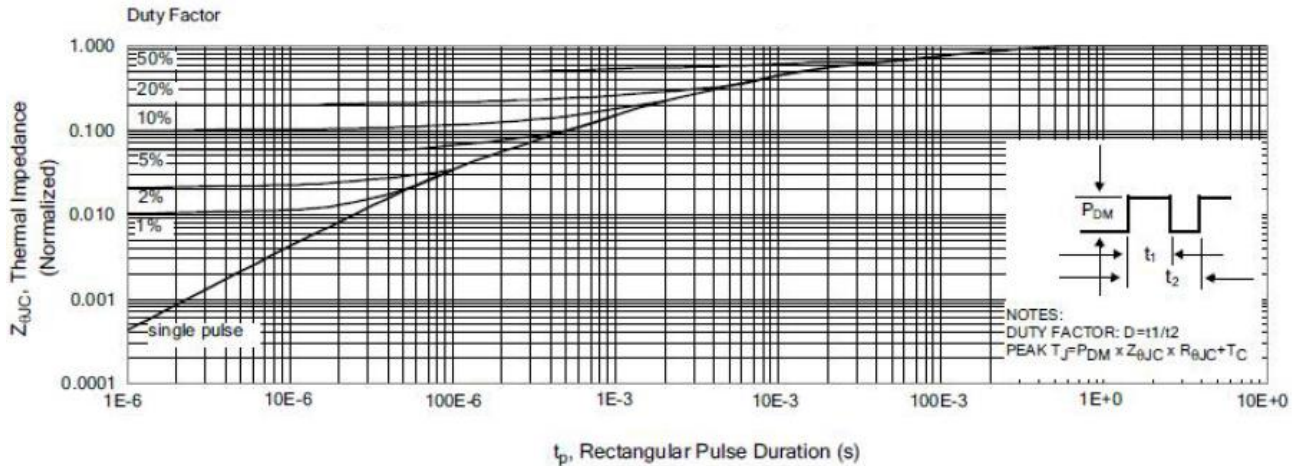


Figure 1. Maximum Effective Thermal Impedance, Junction-to-Case

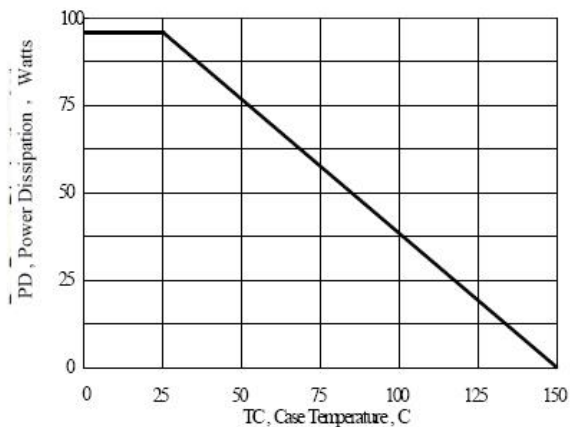


Figure 2. Maximum Power Dissipation vs Case Temperature

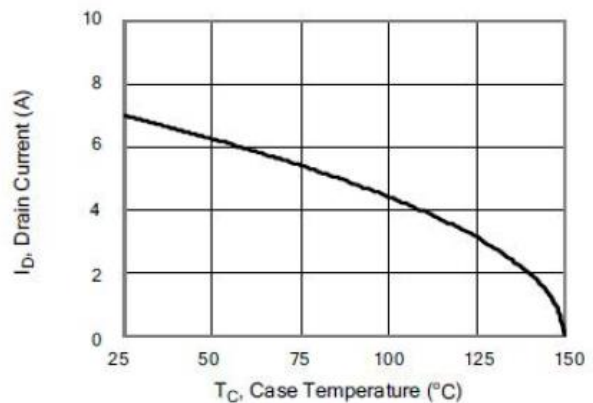


Figure 3. Maximum Continuous Drain Current vs Case Temperature

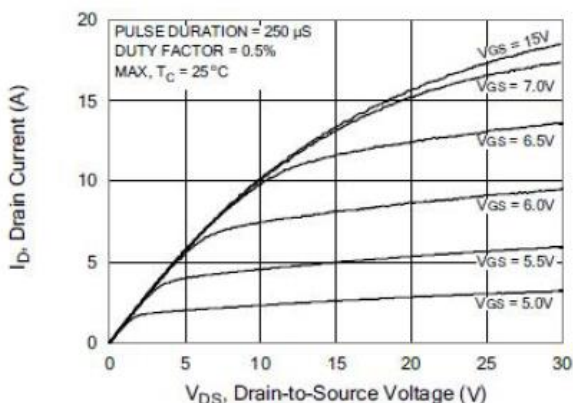


Figure 4. Typical Output Characteristics

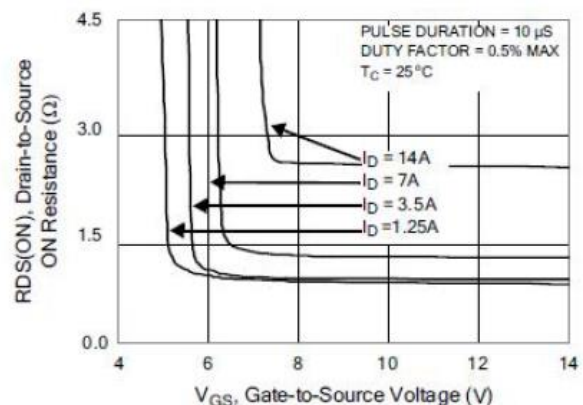


Figure 5. Typical Drain-to-Source ON Resistance vs Gate Voltage and Drain Current

V1.0

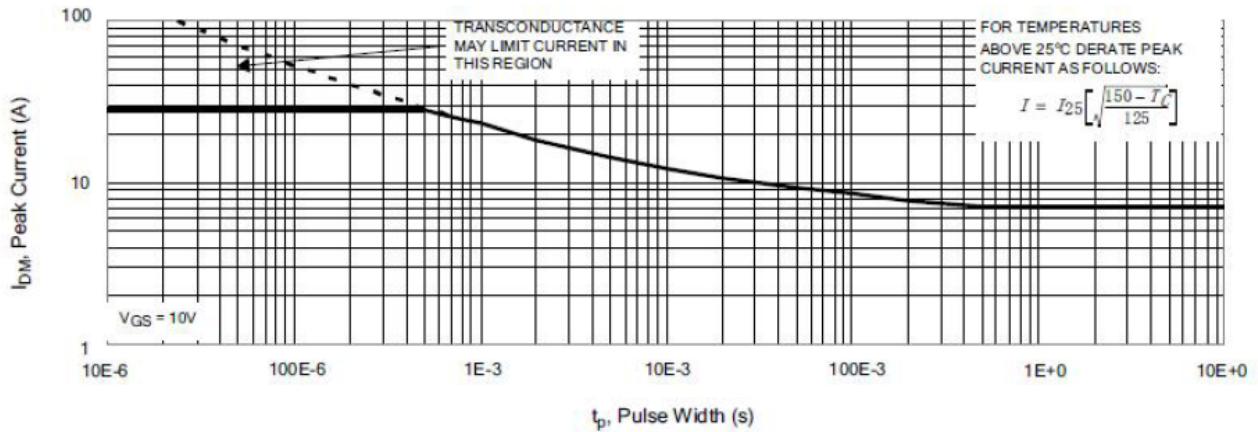


Figure 6. Maximum Peak Current Capability

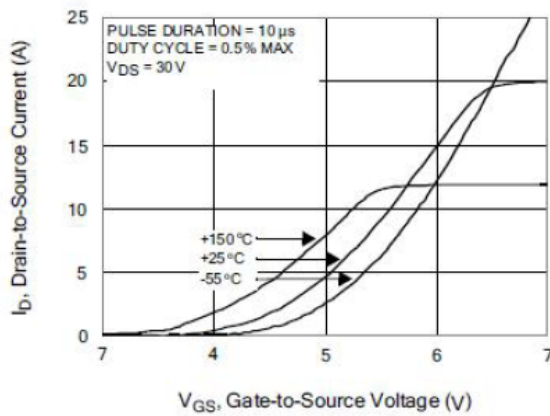


Figure 7. Typical Transfer Characteristics

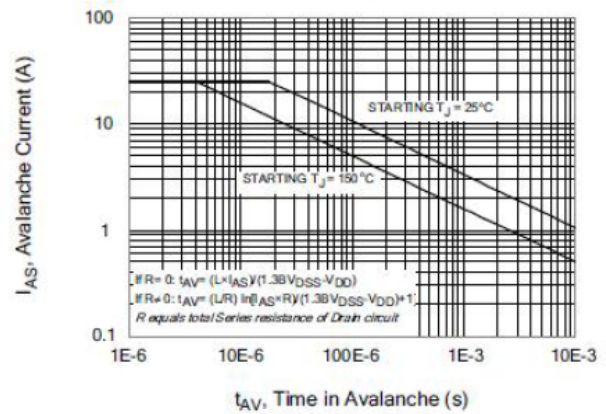


Figure 8. Unclamped Inductive Switching Capability

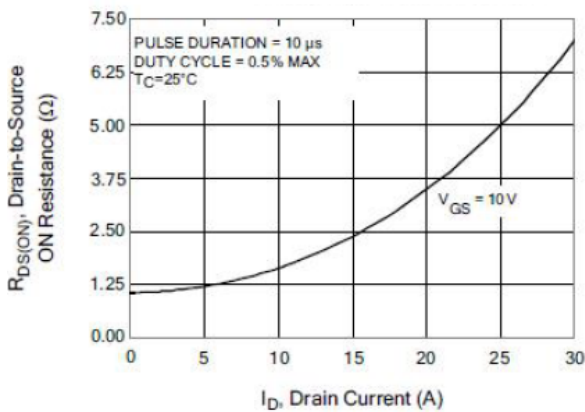


Figure 9. Typical Drain-to-Source ON Resistance vs Drain Current

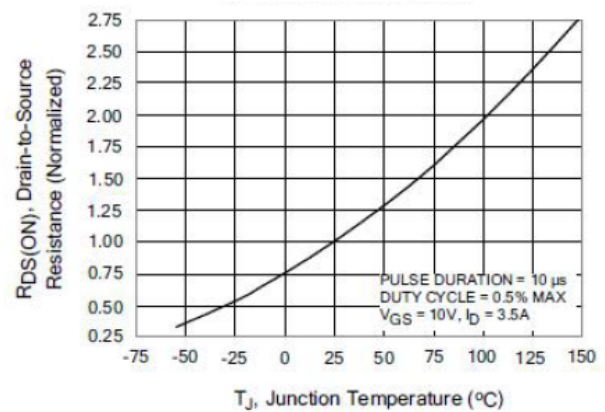


Figure 10. Typical Drain-to-Source ON Resistance vs Junction Temperature

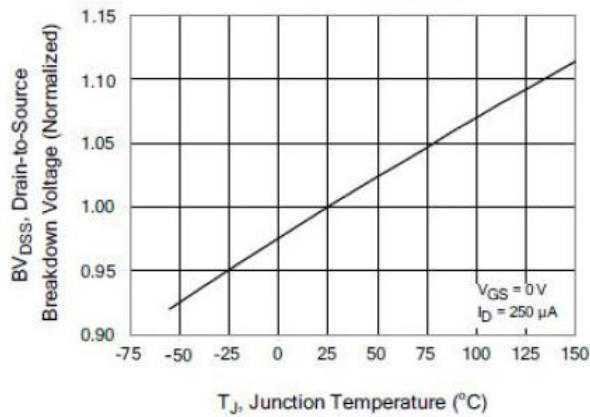


Figure 11. Typical Breakdown Voltage vs Junction Temperature

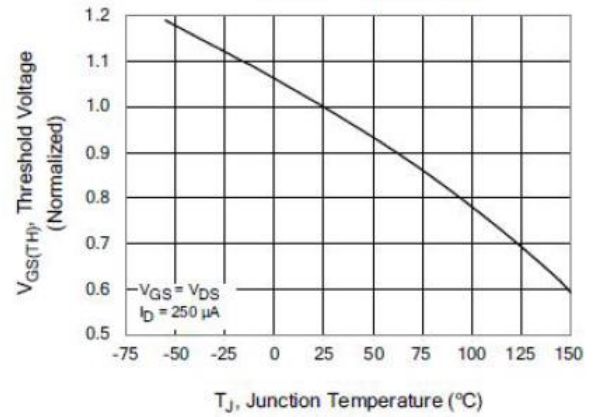


Figure 12. Typical Threshold Voltage vs Junction Temperature

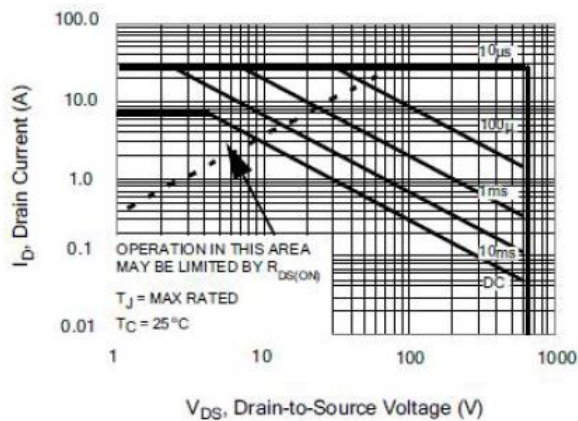


Figure 13. Maximum Forward Bias Safe Operating Area

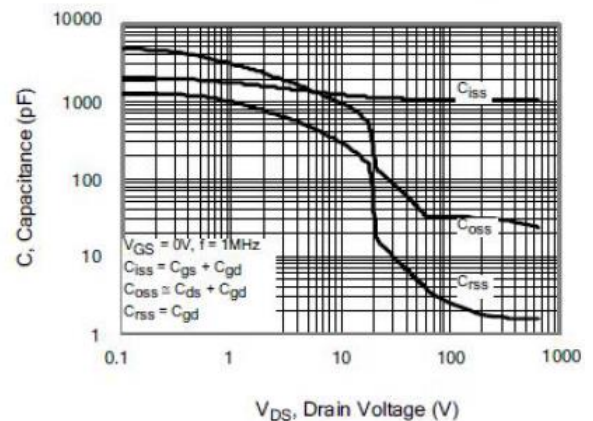


Figure 14. Typical Capacitance vs Drain-to-Source Voltage

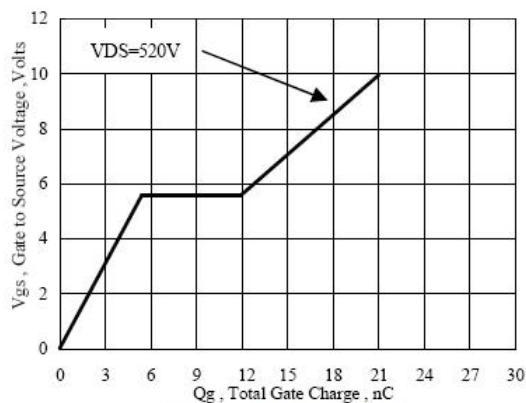


Figure 15. Typical Gate Charge vs Gate-to-Source Voltage

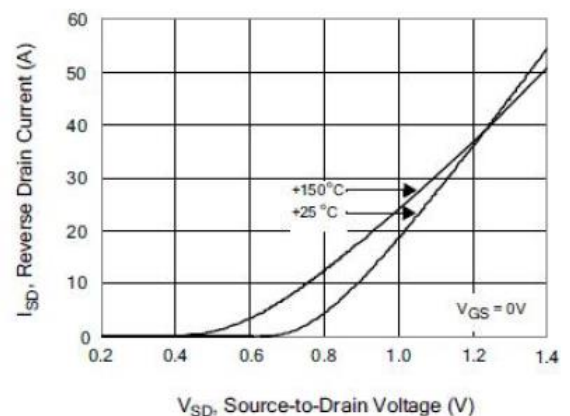
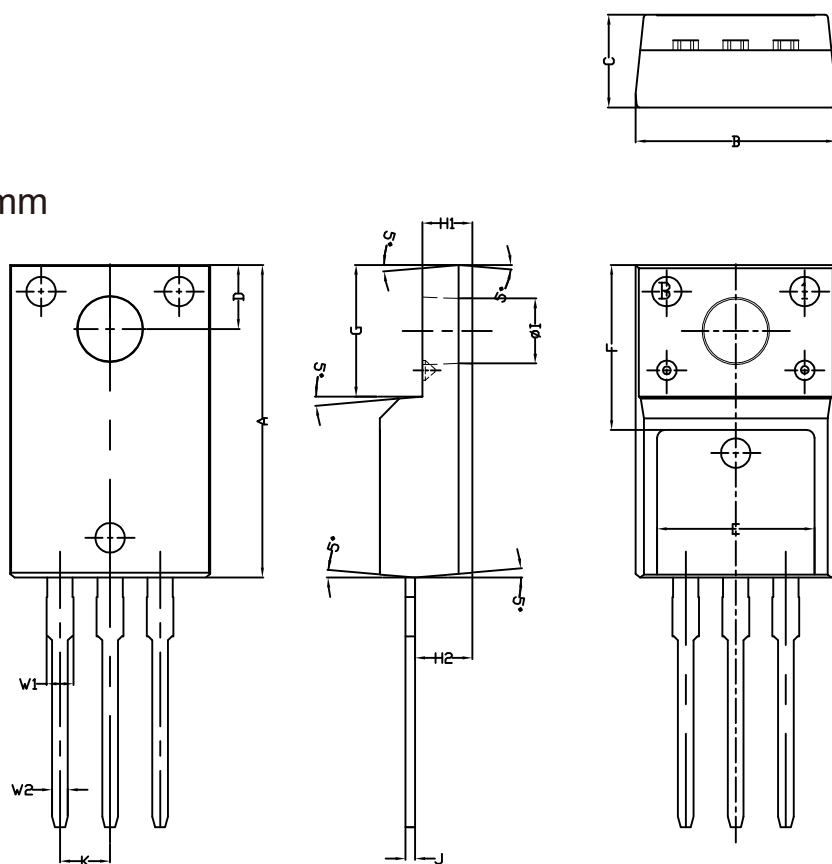


Figure 16. Typical Body Diode Transfer Characteristics

TO-220F Package Information:

Unit:mm



	MM			Inch		
Symbol	Min	Mim	Max	Min	Mim	Max
A	15.67	15,87	16.07	0.6169	0.6248	0.6328
B	9.86	10.16	10.46	0.3882	0.4000	0.4118
C	4.50	4.70	4.90	0.1772	0.1850	0.1929
D	3.15	3.35	3.55	0.1240	0.1319	0.1398
E	7.80	8.00	8.20	0.3071	0.3150	0.3228
F	8.18	8.38	8.58	0.3220	0.3299	0.3378
H1	2.34	2.54	2.84	0.0921	0.1000	0.1118
H2	2.40	2.90	3.40	0.0945	0.1141	0.1339
I	3.10	3.30	3.50	0.1220	0.1299	0.1378
W1	1.08	1.28	1.48	0.0425	0.0504	0.0583
W2	0.70	0.80	0.90	0.0276	0.0315	0.0354
K	2.44	2.54	2.64	0.0961	0.1000	0.1039
G	6.48	6.68	6.88	0.2551	0.2630	0.2709
J	0.45	0.50	0.6	0.0177	0.0197	0.0236

Marking Information:

①. Doingter LOGO

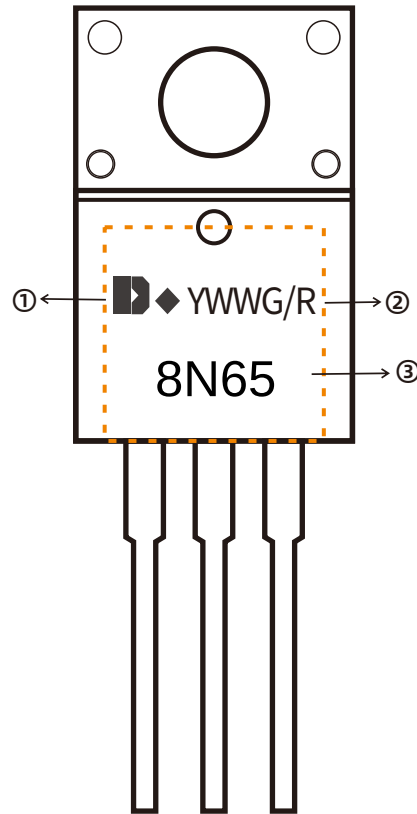
②. Date Code(YWWG / R)

Y : Year Code , last digit of the year

WW : Week Code(01-53)

G/R : G(Green) /R(Lead Free)

③. Part NO.



Previous Version

Version	Date	Subjects (major changes since last revision)
1.0	2022-05-17	Release of final version

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V1.0